



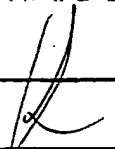
PTO-1449 REPRODUCED  <b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  July 15, 2003  (Use several sheets if necessary)	ATTORNEY DOCKET NO. 0717.1063-007	CONTINUATION OF APPLICATION No. 09/465,140	
	APPLICANT Duy-Phach Vu, et al.		
	FILING DATE	CONFIRMATION NO.	GROUP

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
AR	Akiyama, M., <i>et al.</i> , "Growth of GaAs on Si and Its Application to Fets and LEDs.", <u>Nat. Res. Soc. Symp. Proc.</u> , 67:53-64 (1986).	
AS	Allen, <i>et al.</i> , "Characterization of Isolated Silicon Epitaxy Material", <i>SPIE</i> , Vol. 945 - Advanced Processing of Semiconductor Devices II (3/17-3/18, 1988).	
AT	Conference Record of the 1991 International Display Research Conference, October 15-17, 1991, <i>IEEE</i> .	
AU	Fan, <i>et al.</i> , "Lateral Epitaxy by Seeded Solidification for Growth of Crystal Si Films on Insulators", <u>Appl. Phys. Lett.</u> , 38, 365, 3-1-81.	
AV	McClelland, <i>et al.</i> , "A Technique for Producing Epitaxial Films on Reusable Substrates", <u>Appl. Phys. Lett.</u> , 37, 560, 9-15-80.	
AW	McDaniel, D.L., <i>et al.</i> , "Vertical Cavity Surface-Emitting Semi-Conductor Laser with CW Injection Laser Pumping", <u>IEEE Photon Technol. Lett.</u> , March 23, 1990.	
AX	Milnes, A.G., "Semiconductor Heterojunction Topics: Introduction and Overview", <u>Solid State Electronics</u> , Vol. 29, 2:99-121 (1986).	
AY	Turner, G., <i>et al.</i> , "High-Speed Photoconductive Detectors Fabricated in Heteroepitaxial GaAs Layers", <u>Mat. Res. Soc. Symp. Proc.</u> , 67:181-188 (1986).	
AZ	Weber, J.P., <i>et al.</i> , "Effects of Layer Thickness Variations on Vertical Cavity Surface-Emitting DBR Semiconductor Lasers", <u>IEEE Photon Tech. Ltr.</u> , March 23, 1990.	
AR2	Yablonovitch, <i>et al.</i> , "Extreme Selectivity in the Lift-Off of Epitaxial GaAs Films", <u>Appl. Phys. Lett.</u> , 51, 2222 12-28-87.	
AS2	Sumiyoshi, <i>et al.</i> , Device Layer Transferred Poly Si TFT Array for High Resolution Liquid Crystal Projector", <i>IEEE</i> , 7.3.1-7.3.4, 1989.	
AT2	Y. Hayashi, <i>et al.</i> , "A New Three Dimensional IC Fabrication Technology, Stacking This Film Dual-CMOS Layers", <i>IEEE IDER</i> , pps. 657-660, 1991.	
AU2	"3-D Chip on Chip Stacking", <u>Semiconductor International</u> , December 1991.	

EXAMINER 3/3/03	DATE CONSIDERED 3/3/03
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PTO-1449 REPRODUCED  <b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  July 15, 2003  (Use several sheets if necessary)	ATTORNEY DOCKET NO. 0717.1063-007	CONTINUATION OF APPLICATION No. 09/465,140	
	APPLICANT Duy-Phach Vu, et al.		
	FILING DATE	CONFIRMATION NO.	GROUP

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
	AV2	Matsumoto, et al., "Liquid Crystal Displays (LCDs)", Electronic Display Devices, (John Wiley and Sons) pps. 29-84.
	AW2	
	AX2	
	AY2	

EXAMINER 	DATE CONSIDERED 3/3/05
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